

Search History. 9/27/04. ~~9/27/04~~ (49pp.)

L Number	Hits	Search Text	DB	Time stamp
1	2	("6731531").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/09/27 15:23
2	4	258467.ap.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/09/27 15:24
3	3	903453.ap.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/09/27 15:25
4	5	461593.ap.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/09/27 15:27
5	8	789203.ap.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/09/27 15:45
6	9795	257/77.cccls. 257/314/cccls. 257/315.cccls. 257/316.cccls. 365/185.\$2.cccls.	US-PGPUB	2004/09/27 15:46
7	1700	(257/77.cccls. 257/314/cccls. 257/315.cccls. 257/316.cccls. 365/185.\$2.cccls.) and floating adj gate near5 (sic silicon carbide "Si.sub."\$3"C.sub."\$3)	USPAT; US-PGPUB	2004/09/27 15:46
8	36	(257/77.cccls. 257/314/cccls. 257/315.cccls. 257/316.cccls. 365/185.\$2.cccls.) and floating adj gate near5 (sic silicon adj carbide "Si.sub."\$3"C.sub."\$3)	USPAT; US-PGPUB	2004/09/27 15:47

21	243	(US-4852062-\$ or US-6100193-\$ or US-5990531-\$ or US-6166768-\$ or US-5336361-\$ or US-6271566-\$ or US-6049091-\$ or US-5861346-\$ or US-5828101-\$ or US-5910665-\$ or US-6703264-\$ or US-6228751-\$ or US-6141256-\$ or US-6009018-\$ or US-5754477-\$ or US-5719410-\$ or US-5670790-\$ or US-5672889-\$ or US-5698869-\$ or US-5714766-\$ or US-5640343-\$ or US-5654208-\$ or US-5661312-\$ or US-5625217-\$ or US-5629222-\$ or US-5562769-\$).did. or (US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5530581-\$ or US-5539217-\$ or US-5557114-\$ or US-5557122-\$ or US-5789276-\$ or US-5793697-\$ or US-5734181-\$ or US-5740104-\$ or US-4189826-\$ or US-4373167-\$ or US-4426764-\$ or US-4113515-\$ or US-4657699-\$ or US-4598305-\$ or US-4460670-\$ or US-4462150-\$ or US-4473836-\$ or US-4451391-\$ or US-4826778-\$ or US-4738729-\$ or US-4768072-\$ or US-4507673-\$ or US-5506421-\$ or US-5455432-\$).did. or (US-5465249-\$ or US-6108177-\$ or US-5369040-\$ or US-5393999-\$ or US-5371383-\$ or US-5323040-\$ or US-5298796-\$ or US-5293560-\$ or US-5260560-\$ or US-5260593-\$ or US-5159424-\$ or US-5235195-\$ or US-5145741-\$ or US-5061976-\$ or US-5111430-\$ or US-5049950-\$ or US-5039354-\$ or US-5056897-\$ or US-5477485-\$ or US-5449941-\$ or US-5451798-\$ or US-5407845-\$ or US-5408377-\$ or US-5415126-\$ or US-5441901-\$ or US-5449925-\$ or US-6099574-\$).did. or (US-5508543-\$ or US-6011279-\$ or US-5976926-\$ or US-5907775-\$ or US-5932902-\$ or US-5959896-\$ or US-5886368-\$ or US-5886376-\$ or US-5886379-\$ or US-5898197-\$ or US-5877041-\$ or US-5852306-\$ or US-5858811-\$ or US-5866930-\$ or US-5798548-\$ or US-5808336-\$ or US-5846859-\$ or US-5786250-\$ or US-6002143-\$ or US-5989958-\$ or US-6075259-\$ or US-6031263-\$ or US-6018166-\$ or US-5030580-\$ or US-4994401-\$ or US-4943838-\$ or US-4769686-\$).did. or (US-4841349-\$ or US-4849797-\$ or US-4893273-\$ or US-6133587-\$ or US-6141260-\$ or US-6144581-\$ or US-6049110-\$ or US-6034001-\$ or US-6125062-\$ or US-6180958-\$ or US-6246606-\$ or US-6236590-\$ or US-6178112-\$ or US-6166948-\$ or US-6197439-\$ or US-6140181-\$ or US-6166319-\$ or US-6163066-\$ or US-6166401-\$ or US-6133120-\$ or US-6130147-\$ or US-6084248-\$ or US-6093937-\$ or US-6754108-\$ or US-6121633-\$ or US-6313482-\$ or US-6309907-\$).did. or (US-6344663-\$ or US-6365919-\$ or US-6351411-\$ or US-6452831-\$ or US-6407426-\$ or US-6407424-\$ or US-6383576-\$ or US-6465375-\$ or US-6452839-\$ or US-6514820-\$ or US-6492694-\$ or US-6562131-\$ or US-6537371-\$ or US-6731551-\$ or US-6734510-\$ or US-6586797-\$ or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/27 15:59
Search History	9/27/04 1:59:49 PM	Page 2		
H:\EASTBACK\09691004	US-6734510-\$ or US-6586797-\$ or			

22	70	((US-4852062-\$ or US-6100193-\$ or US-5990531-\$ or US-6166768-\$ or US-5336361-\$ or US-6271566-\$ or US-6049091-\$ or US-5861346-\$ or US-5828101-\$ or US-5910665-\$ or US-6703264-\$ or US-6228751-\$ or US-6141256-\$ or US-6009018-\$ or US-5754477-\$ or US-5719410-\$ or US-5670790-\$ or US-5672889-\$ or US-5698869-\$ or US-5714766-\$ or US-5640343-\$ or US-5654208-\$ or US-5661312-\$ or US-5625217-\$ or US-5629222-\$ or US-5562769-\$).did. or (US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5530581-\$ or US-5539217-\$ or US-5557114-\$ or US-5557122-\$ or US-5789276-\$ or US-5793697-\$ or US-5734181-\$ or US-5740104-\$ or US-4189826-\$ or US-4373167-\$ or US-4426764-\$ or US-4113515-\$ or US-4657699-\$ or US-4598305-\$ or US-4460670-\$ or US-4462150-\$ or US-4473836-\$ or US-4451391-\$ or US-4826778-\$ or US-4738729-\$ or US-4768072-\$ or US-4507673-\$ or US-5506421-\$ or US-5455432-\$).did. or (US-5465249-\$ or US-6108177-\$ or US-5369040-\$ or US-5393999-\$ or US-5371383-\$ or US-5323040-\$ or US-5298796-\$ or US-5293560-\$ or US-5260560-\$ or US-5260593-\$ or US-5159424-\$ or US-5235195-\$ or US-5145741-\$ or US-5061976-\$ or US-5111430-\$ or US-5049950-\$ or US-5039354-\$ or US-5056897-\$ or US-5477485-\$ or US-5449941-\$ or US-5451798-\$ or US-5407845-\$ or US-5408377-\$ or US-5415126-\$ or US-5441901-\$ or US-5449925-\$ or US-6099574-\$).did. or (US-5508543-\$ or US-6011279-\$ or US-5976926-\$ or US-5907775-\$ or US-5932902-\$ or US-5959896-\$ or US-5886368-\$ or US-5886376-\$ or US-5886379-\$ or US-5898197-\$ or US-5877041-\$ or US-5852306-\$ or US-5858811-\$ or US-5866930-\$ or US-5798548-\$ or US-5808336-\$ or US-5846859-\$ or US-5786250-\$ or US-6002143-\$ or US-5989958-\$ or US-6075259-\$ or US-6031263-\$ or US-6018166-\$ or US-5030580-\$ or US-4994401-\$ or US-4943838-\$ or US-4769686-\$).did. or (US-4841349-\$ or US-4849797-\$ or US-4893273-\$ or US-6133587-\$ or US-6141260-\$ or US-6144581-\$ or US-6049110-\$ or US-6034001-\$ or US-6125062-\$ or US-6180958-\$ or US-6246606-\$ or US-6236590-\$ or US-6178112-\$ or US-6166948-\$ or US-6197439-\$ or US-6140181-\$ or US-6166319-\$ or US-6163066-\$ or US-6166401-\$ or US-6133120-\$ or US-6130147-\$ or US-6084248-\$ or US-6093937-\$ or US-6754108-\$ or US-6121633-\$ or US-6313482-\$ or US-6309907-\$).did. or (US-6344663-\$ or US-6365919-\$ or US-6351411-\$ or US-6452831-\$ or US-6407426-\$ or US-6407424-\$ or US-6383576-\$ or US-6465375-\$ or US-6452839-\$ or US-6514820-\$ or US-6492694-\$ or US-6562131-\$ or US-6537371-\$ or US-6731531-\$ or US-6734510-\$ or US-6586797-\$ or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/27 15:59
Search History	9/27/04 11:59:49 PM	Page 1 of 1		
H:\EASTBACK\09691004	US-6537371-\$ or US-6731531-\$ or US-6734510-\$ or US-6586797-\$ or			

-	13	(("4113515") or ("4473836") or ("5698869") or ("5858811") or ("5976926") or ("6031263") or ("6084248") or ("6093937") or ("6099574") or ("6130147") or ("6144581") or ("6163066") or ("6166401")).PN.	USPAT	2004/09/25 14:16
-	13	(US-6144581-\$ or US-6163066-\$ or US-6166401-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$).did.	USPAT	2002/05/10 11:29
-	1	hartstein.in. and low adj voltage adj memory.ti.	EPO	2002/05/10 11:28
-	0	jp-63289960\$--.did.	USPAT	2002/05/10 11:30
-	0	jp-363289960\$--.did.	USPAT	2002/05/10 11:30
-	0	jp-0363289960\$--.did.	USPAT	2002/05/10 11:34
-	1	takashi.in. and carrier near6 silicon adj substrate	USPAT	2002/05/10 11:36
-	3	takashi.in. and carrier near6 silicon adj substrate	JPO	2002/05/10 11:38
-	38	diamond adj layer near6 process	DERWENT	2002/05/10 11:39
-	2	(diamond adj layer near6 process) and silicon adj carbide	DERWENT	2002/05/10 11:45
-	1	takashi.in. and ito.in. and igfet	EPO	2002/05/10 11:45
-	0	jp-063219172\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/10 11:47
-	2	jp-63219172\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/10 12:15
-	2	jp-63289960\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/10 11:49
-	2	jp-01115162\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/10 11:49
-	2	jp-63181473\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/10 11:50
-	2	jp-62122275\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/10 11:51
-	0	jp-404056769\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/10 11:52
-	2	jp-04056769\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/10 12:02
-	796	(257/77).CCLS.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:04

	9	((257/77).CCLS.) and (x near12 silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:18
	489	silicon adj carbide and gate and x and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:19
	53	silicon adj carbide.ti,ab. and gate and x and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:26
	162	stoichiometric adj coefficient	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:26
	11	stoichiometric adj coefficient near x	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:26
	30	stoichiometric adj coefficient near12 x	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:28
	0	"si.sub.1-x.c.sub.x" and field adj effect adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:30
	0	"si.sub.1-x.c.sub.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:29
	57	"si.sub.1-x" adj "c.sub.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:31
	18	"si.sub.1-x" adj "c.sub.x" and (mosfet or fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 13:55
	15	"si.sub.1-x" adj "c.sub.x" and (mosfet or fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or (gate and (source or drain)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 13:57
	179	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:07
	50	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:15

		1	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier adj energy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:10
		30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:24
		0	((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:26
		0	((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:20
		0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:20
		0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:20
		0	((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:27
		30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:49
		30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) and x and (source same drain) and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:51
		53	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:52
	2616		(silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:53

-		133	(silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.cccls. or 438/\$6.cccls. or 361/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:54 2002/05/10 14:55 2002/05/10 15:05 2002/05/10 15:09
-		133	(silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near6 gate) near12 x and (257/\$6.cccls. or 438/\$6.cccls. or 361/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:55
-		2	((silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" near6 gate) near12 x and (257/\$6.cccls. or 438/\$6.cccls. or 361/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:05
-		0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) near12 x and (257/\$6.cccls. or 438/\$6.cccls. or 361/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:09
-		0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate) near12 (x or y or a or b) and (257/\$6.cccls. or 438/\$6.cccls. or 361/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:35
-		1	(("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate) near12 (x or y or a or b) and (257/\$6.cccls. or 438/\$6.cccls. or 361/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:12
-		684	(silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-b)c(b)" or "si.1-a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:13
-		161	((silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.cccls. ("6249020").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:42
-		2	("6031263").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:24
-		2	("6049110").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 17:09
-		2	("6049110").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 17:09

-	0	((si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:33
-	0	((si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:33
-	51	(US-5451798-\$ or US-6166319-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$ or US-6166401-\$ or US-5661312-\$ or US-5719410-\$ or US-5798548-\$ or US-5801401-\$ or US-6011279-\$ or US-6049110-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-6249020-\$ or US-6344663-\$).did. or (US-5886368-\$ or US-6383576-\$ or US-4826778-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$).did. or (US-20010032997-\$ or US-20010049183-\$).did. or (EP-681333-\$ or EP-291951-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-63289960-\$ or JP-56056677-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or EP-276002-\$ or EP-291951-\$ or JP-01115162-\$ or JP-07115191-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/05/10 18:34
-	351	silicon near3 doped near6 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:36
-	45	(silicon near3 doped near6 carbon) and (257/\$6.ccls. or 438/\$6.ccls.) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:38
-	4	((silicon near3 doped near6 carbon) near12 gate) and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:40
-	5	((silicon near3 dop\$3 near6 carbon) near12 gate) and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:41
-	235	((carbon or silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:43

-	74	((carbon or silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.cccls.) not ((silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 20:13
-	0	silicon-doped adj carbon adj (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 20:13
-	0	si-doped adj carbon adj (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 20:14
-	201	((c or carbon) near (si or silicon)) adj (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 20:15
-	10092	((c or carbon) near6 (si or silicon)) near6 (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 20:16
-	3434	(carbon near6 (si or silicon)) near6 (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 20:16
-	118	(carbon near1 (si or silicon)) near3 (film or electrode) and (257/\$6.cccls. or 438/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 21:21
-	0	polysilicon/carbon near12 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 21:22
-	0	"polysilicon/carbon" near12 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 21:22
-	0	(polysilicon near1 carbon) near12 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 21:23
-	1	(silicon near1 carbon) near12 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 21:49
-	6	p-doped adj silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 21:30

	7	P-dopant near12 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 21:49
-	0	carbon adj doping adj2 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:21
-	4	silicon adj doping adj2 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:27
-	0	p-doped adj silicon adj carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:27
-	7	p-doped adj2 silicon adj2 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:28
-	1	(p-doped or p-doping) near12 silicon adj carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:31
-	0	"si.sub.1-x.c.sub.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:35
-	57	"si.sub.1-x c.sub.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:43
-	0	"si.sub.1-x c.sub.x" near20 (work adj function or workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:43
-	2	"si.sub.1-x c.sub.x" near20 (barrier or work adj function or workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:48
-	1	"si.sub.x c.sub.1-x" near20 (barrier or work adj function or workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:49
-	10	"si.sub.1-x c.sub.x" near20 (electrode or conductivity or conduction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 17:04
-	1	("si.sub.1-x c.sub.x" or "si.sub.x c.sub.1-x" or "si.sub.1-y c.sub.y" or "si.sub.y c.sub.1-y") near20 electron adj affinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 20:09
-	0	resistivity near4 "si.sub.1-x. c.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 20:26

	965	(conductivity or resistivity) near12 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/11 20:39
	0	(conductivity or resistivity) near12 "si.sub.1-x c.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/11 21:10
	8	barrier adj energy near12 silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/11 21:14
	0	barrier adj energy near12 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/11 21:20
	108	barrier adj energy.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/11 21:23
	2	barrier adj energy near12 (sic or "si.sub.1-x. c.x" or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/11 21:24
	21	(resistivity or conductivity) near12 (silicon adj carbide or "si.sub.1-x. c.sub.x" or "si.sub.x. c.sub.1-x") near12 x	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/12 12:26
	17	barrier adj energy near12 gate near12 insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/12 12:07
	3	("5661312").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/12 12:10
	0	("floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/12 12:10
	30	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/12 12:11
	0	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and photodetection	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/12 12:12
	30	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/12 12:21
	18	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/05/12 12:21

-		18	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory and (barrier adj energy or potential adj barrier or tunneling adj barrier or interface adj barrier or barrier) ("5886368").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:23
-		3		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 17:44
-		3	("5661312").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 17:46
-		46061	polycrystalline near12 silicon carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field adj effect adj transistor) and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 17:48
-		13	polycrystalline near12 silicon adj carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field adj effect adj transistor) and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 17:50
-		22	(polycrystalline or monocrystalline) near12 silicon adj carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field adj effect adj transistor) and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 17:51
-		4	(polycrystalline or monocrystalline) near12 silicon adj carbide near12 gate and (mosfet or fet or nmosfet or pmosfet or cmosfet or field adj effect adj transistor) and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 17:52
-		24	(polycrystalline or monocrystalline) near12 silicon adj carbide near12 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 18:16
-		3	("5369040").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 18:17
-		10	floating adj gate near12 control adj gate and photodetect\$3 and (mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or transistor or field adj effect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 18:30
-		0	floating adj gate near12 control adj gate near12 silicon adj carbide and photodetect\$3 and (mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or transistor or field adj effect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 18:31
-		0	floating adj gate near12 control adj gate near12 silicon adj carbide and photodetect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 18:31
-		0	floating adj gate near12 control adj gate near12 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 18:32
-		2	floating adj gate near12 control adj gate near12 (sic or silicon adj carbide or "si.sub.1-x. c.sub.x")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 18:56

	52	((("4460670") or ("4462150") or ("4507673")) or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.	USPAT	2002/05/13 17:30
	6	((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.) and ("si.sub.1-x. c.sub.x" or "si.sub.1-y. c.sub.y" or "si.sub.x c.sub.1-x" or "si.sub.y c.sub.1-y" or silicon carbide or sic) and source and drain and floating adj gate and control adj gate and silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 18:18

-	0	((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.) and ("si.sub.1-x. c.sub.x" or "si.sub.1-y. c.sub.y" or "si.sub.x c.sub.1-x" or "si.sub.y c.sub.1-y") and source and drain and floating adj gate and control adj gate and silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 20:34
-	588	(257/77).CCLS.	USPAT; US-PGPUB	2002/05/13 20:34
-	118	(257/153).CCLS.	USPAT; US-PGPUB	2002/05/13 20:34
-	402	(257/314).CCLS.	USPAT; US-PGPUB	2002/05/13 20:39
-	782	(257/315).CCLS.	USPAT; US-PGPUB	2002/05/13 20:39
-	943	(257/316).CCLS.	USPAT; US-PGPUB	2002/05/13 20:40
-	2311	((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 20:40
-	357	((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.)) and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 20:44
-	90	((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.)) and (silicon adj carbide near15 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 21:12
-	2	("5989958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 21:12

	115	(US-5449941-\$ or US-5455432-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$ or US-5451798-\$ or US-5734181-\$ or US-6166319-\$ or US-6383576-\$ or US-5801401-\$ or US-5989958-\$ or US-6344663-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$).did. or (US-6166401-\$ or US-5465249-\$ or US-4451391-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-5661312-\$ or US-5798548-\$ or US-6011279-\$ or US-6049110-\$ or US-6249020-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-5719410-\$ or US-5886368-\$ or US-4826778-\$ or US-6351411-\$ or US-5557114-\$ or US-5562769-\$ or US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5629222-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$).did. or (US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5886379-\$ or US-5907775-\$ or US-6018166-\$ or US-6034001-\$ or US-6075259-\$ or US-5557122-\$ or US-5866930-\$ or US-5898197-\$ or US-5808336-\$ or US-5393999-\$ or US-5539217-\$ or US-4460670-\$ or US-4462150-\$ or US-4507673-\$ or US-4657699-\$ or US-4738729-\$ or US-4768072-\$ or US-4769686-\$ or US-4841349-\$ or US-4849797-\$ or US-4893273-\$).did. or (US-5049950-\$ or US-5111430-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$ or US-5293560-\$ or US-5298796-\$ or US-5371383-\$ or US-5407845-\$ or US-5415126-\$ or US-5508543-\$ or US-5530581-\$ or US-5477485-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020017647-\$).did. or (EP-291951-\$ or EP-681333-\$).did. or (JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-04056769-\$ or JP-63289960-\$ or JP-57126175-\$ or JP-04061170-\$ or JP-56056677-\$ or JP-02203564-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-01115162-\$ or EP-291951-\$ or EP-276002-\$ or JP-07115191-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/05/14 08:24
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	1	((US-5449941-\$ or US-5455432-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$ or US-5451798-\$ or US-5734181-\$ or US-6166319-\$ or US-6383576-\$ or US-5801401-\$ or US-5989958-\$ or US-6344663-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$).did. or (US-6166401-\$ or US-5465249-\$ or US-4451391-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-5661312-\$ or US-5798548-\$ or US-6011279-\$ or US-6049110-\$ or US-6249020-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-5719410-\$ or US-5886368-\$ or US-4826778-\$ or US-6351411-\$ or US-5557114-\$ or US-5562769-\$ or US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5629222-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$).did. or (US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5886379-\$ or US-5907775-\$ or US-6018166-\$ or US-6034001-\$ or US-6075259-\$ or US-5557122-\$ or US-5866930-\$ or US-5898197-\$ or US-5808336-\$ or US-5393999-\$ or US-5539217-\$ or US-4460670-\$ or US-4462150-\$ or US-4507673-\$ or US-4657699-\$ or US-4738729-\$ or US-4768072-\$ or US-4769686-\$ or US-4841349-\$ or US-4849797-\$ or US-4893273-\$).did. or (US-5049950-\$ or US-5111430-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$ or US-5293560-\$ or US-5298796-\$ or US-5371383-\$ or US-5407845-\$ or US-5415126-\$ or US-5508543-\$ or US-5530581-\$ or US-5477485-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020017647-\$).did. or (EP-291951-\$ or EP-681333-\$).did. or (JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-04056769-\$ or JP-63289960-\$ or JP-57126175-\$ or JP-04061170-\$ or JP-56056677-\$ or JP-02203564-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-01115162-\$ or EP-291951-\$ or EP-276002-\$ or JP-07115191-\$).did.) and ohba.in. (257/77).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 08:34
	799	("5989958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 08:53
	2	("5989958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 10:54

	469	(257/314).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 09:08
	467	((257/314).CCLS.) not ((257/77).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 09:24
	1816	257/315	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 09:24
	1577	(257/315 not (((257/314).CCLS.) not ((257/77).CCLS.))) not ((257/77).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 09:26
	1375	(257/316).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 10:54
	858	(((257/316).CCLS.) not 257/315) not (((257/314).CCLS.) not ((257/77).CCLS.))) not ((257/77).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 10:55
	0	("jp-3222367\$-\$ did.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:45
	2	jp-03222367\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:46
	13	jp-0224431\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:46
	2	jp-06224431\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:47
	10	jp-302828\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:48
	2	jp-06302828\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:48
	2	jp-07226507\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:49
	2	jp-08255878\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:50

	0	jp-08255878TR\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/14 12:50
	0	jp-08255878-TR\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/14 12:50
	2	jp-60184681\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/14 12:52
	2	jp-60242678\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/14 12:52
	4	method adj2 using.clm. and optical adj switch.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/14 13:29
	714	(257/295).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 13:13
	0	("mram.ti,ab.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 13:13
	276	mram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 13:21
	988	((257/295).CCLS.) or mram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 13:21
	873	magnetic adj memory adj device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 13:32
	4	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 13:38
	8	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 14:56
	1	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj2 (layer or film) same orient\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 15:06
	1846	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:14

	2	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 15:51
	1	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) and coercivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 15:59
	0	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) and coercivity and ferrimagnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:01
	719	((257/295).CCLS.) or (magnetic adj memory adj device) and af adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:17
	44	(365/172).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:35
	283	(365/173).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:35
	804	((365/171) or (365/172) or (365/173)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 18:02
	0	((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity and (data adj storage near3 (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 18:08
	4	((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity	USPAT; US-PGPUB	2002/05/15 18:10
	4	((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	USPAT; US-PGPUB	2002/05/15 19:32
	0	((365/171) or (365/172) or (365/173)).CCLS.) and ((synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) near6 (layer or film))	USPAT; US-PGPUB	2002/05/15 18:31
	0	((365/171) or (365/172) or (365/173)).CCLS.) and (synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic)	USPAT; US-PGPUB	2002/05/15 18:31
	23	(synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) and (mram or magnetic adj memory)	USPAT; US-PGPUB	2002/05/15 18:36
	2	(synthetic adj (ferrimagnet or ferrimagnetic) or sf or artificial adj ferrimagnetic) and (mram or magnetic adj memory).ti,ab.	USPAT; US-PGPUB	2002/05/15 18:38

	4	((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	USPAT; US-PGPUB	2002/05/15 19:44
	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	USPAT; US-PGPUB	2002/05/15 19:46
	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 19:48
	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 19:48
	17	(antiferrimagnetic or femn or af) and (magnetic adj memory) and coercivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 19:51
	8934	(antiferrimagnetic or femn or af) and (hs mtj or hard-soft adj mtj)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 19:52
	1	(antiferrimagnetic or femn or af) and (hs adj mtj or hard-soft adj mtj)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 21:17
	1	"5966012".PN.	USPAT	2002/05/15 20:52
	1	"5841692".PN.	USPAT	2002/05/15 20:55
	1	"5801984".PN.	USPAT	2002/05/15 20:56
	1	"5055158".PN.	USPAT	2002/05/15 20:57
	1	"5055158".PN.	USPAT	2002/05/15 20:58
	1	(antiferromagnetic or femn or af) and (hs adj mtj or hard-soft adj mtj)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 21:24
	2	("5605958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 21:24
	3	("5650958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 22:05
	77	magnetic adj memory and spacer adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 22:29
	0	magnetic adj memory and (spacer adj layer near12 sf)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 22:30

	77	magnetic adj memory and spacer adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 22:48
	7	magnetic adj memory and (spacer adj layer near5 antiferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 07:45
	3	magnetic adj memory and (spacer adj layer near5 antiferromagnetic) and (spacer near12 different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:01
	0	(spacer near12 antiferromagnetic near12 different) and magnetic adj2 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:02
	5	spacer near12 antiferromagnetic near12 different	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:45
	295	(365/158).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:45
	602	(365/171).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:46
	44	(365/172).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:46
	283	(365/173).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:46
	3429	(365/174).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:46
	431	(257/30).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:47
	4807	((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:47
	179	spacer and coercivity and antiferromagnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 08:48
	11	((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)) and (spacer and coercivity and antiferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 13:56

-	5	((((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)) and (spacer and coercivity and antiferromagnetic)) and @pd<20000104	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 14:30
-	0	mtj adj mr and world adj line and bottom adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 14:31
-	0	mtj adj mr and world adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 14:32
-	1	mtj adj mr and word adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 14:33
-	7	"6114719"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 15:30
-	3	mtj and (current near12 (magnetization or magnetized)) near12 (perpendicular or orthogonal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 16:37
-	0	"not pinned" and (mram or mtj)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 16:44
-	0	"not pinned" and (mram or mtj or magneto-resistive or af adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 16:45
-	178	(hard same soft) and (mram or mtj or magneto-resistive or af adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 16:47
-	0	(soft-soft) and (mram or mtj or magneto-resistive or af adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 16:47
-	0	soft-soft and (mtj or mram or magneto-resistive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 16:49
-	11	soft-soft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 16:50
-	0	soft-soft and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 16:50
-	3	mtj and second adj free	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/16 20:54

-	17	(spacer near12 (ru or ruthenium)) near12 (af adj layer reference adj layer or data adj layer or sens\$3 adj layer or pinned adj2 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/05/16 22:40
-	3	(("5640343") or ("6269018") or ("5966012")).PN.	USPAT;	2002/05/16 23:13
-	2	903452.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 11:23
-	2	("5989958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 12:57
-	0	jp-03571261\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 12:58
-	8	hamakawa.in. and silicon and carbide and semiconductor	IBM TDB JPO	2002/11/04 13:00
-	2	"3571261"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 12:59
-	1	"carbide/amorphous".ti.	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 15:49
-	0	optoelectric adj conversion and electron adj affinity	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 18:04
-	329	optoelectric adj conversion	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 18:04
-	2724	electron adj affinity	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 18:04
-	0	optoelectric adj conversion near12 affinity	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 18:05
-	32	optoelectric adj conversion near12 efficiency	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 18:06
-	4	optoelectric adj conversion near12 efficiency and silicon adj carbide	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 18:07
-	3404	((257/77) or (257/314) or (257/315) or (257/316)).CCLS.	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/05 11:44

-		14	((257/77) or (257/314) or (257/315) or (257/316)).CCLS.) and breakdown adj voltage near15 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/05 11:46
-		1	((257/77) or (257/314) or (257/315) or (257/316)).CCLS.) and electron adj affinity near15 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/05 11:47
-		2	("6104054").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/05 14:24
-		8	(("5661312") or ("5798548") or ("5989958") or ("5808336") or ("5369040") or ("5557122") or ("5393999") or ("5734181")).PN.	USPAT	2003/01/27 10:34
-		0	jp-357126175\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/01/27 10:38
-		2	jp-57126175\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/01/27 10:40
-		2	jp-02203564\$-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/01/27 10:40
-		13	(US-6084248-\$ or US-6031263-\$ or US-5976926-\$ or US-5858811-\$ or US-5698869-\$ or US-4473836-\$ or US-4113515-\$ or US-6130147-\$ or US-6144581-\$ or US-6099574-\$ or US-6093937-\$ or US-6166401-\$ or US-6163066-\$).did.	USPAT	2003/03/21 13:50
-		57	hamakawa.in. and conversion	USPAT; JPO	2003/03/21 13:51
-		0	hamakawa.in. and conversion and optoelectronic	JPO	2003/03/21 13:51
-		1	hamakawa.in. and conversion and heterojunction	JPO	2003/03/21 13:52
-		31	hamakawa.in. and conversion	JPO	2003/03/21 13:52

	141	(US-5449941-\$ or US-6383576-\$ or US-6166319-\$ or US-5451798-\$ or US-5734181-\$ or US-5260560-\$ or US-5886379-\$ or US-5786250-\$ or US-5877041-\$ or US-5846859-\$ or US-5789276-\$ or US-5754477-\$ or US-5740104-\$ or US-5670790-\$ or US-5714766-\$ or US-5654208-\$ or US-5623442-\$ or US-5580380-\$ or US-5604357-\$ or US-5562769-\$ or US-5557114-\$ or US-5530581-\$ or US-5477485-\$ or US-5455432-\$ or US-5407845-\$ or US-5415126-\$).did. or (US-5298796-\$ or US-5293560-\$ or US-5260593-\$ or US-5235195-\$ or US-5145741-\$ or US-5111430-\$ or US-5049950-\$ or US-4893273-\$ or US-4841349-\$ or US-4769686-\$ or US-4738729-\$ or US-4657699-\$ or US-4462150-\$ or US-4460670-\$ or US-6002143-\$ or US-5852306-\$ or US-4849797-\$ or US-5369040-\$ or US-5039354-\$ or US-5159424-\$ or US-5056897-\$ or US-4826778-\$ or US-5886368-\$ or US-5719410-\$ or US-5371383-\$ or US-6236590-\$ or US-6166948-\$).did. or (US-5793697-\$ or US-5640343-\$ or US-6205052-\$ or US-6178112-\$ or US-6197439-\$ or US-6108177-\$ or US-5408377-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6249020-\$ or US-6018166-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-5661312-\$ or US-5539217-\$ or US-5465249-\$ or US-5323040-\$ or US-4507673-\$ or US-5625217-\$ or US-5061976-\$ or US-6344663-\$ or US-6180958-\$).did. or (US-5989958-\$ or US-5801401-\$ or US-5393999-\$ or US-5629222-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-6351411-\$ or US-5898197-\$ or US-5508543-\$ or US-5808336-\$ or US-5866930-\$ or US-5557122-\$ or US-6034001-\$ or US-5907775-\$ or US-6166401-\$ or US-6163066-\$ or US-6144581-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6031263-\$ or US-6084248-\$ or US-5976926-\$ or US-5698869-\$ or US-4113515-\$ or US-4473836-\$).did. or (US-5858811-\$).did. or (US-20020017647-\$ or US-20020036331-\$ or US-20020041514-\$ or US-20020024050-\$ or US-20010049183-\$ or US-20010032997-\$).did. or (EP-291951-\$ or US-5585986-\$ or EP-681333-\$).did. or (JP-63219172-\$ or JP-01115162-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-04061170-\$ or JP-57126175-\$ or JP-06224431-\$ or JP-63289960-\$).did. or (EP-276002-\$ or JP-07115191-\$ or JP-62122275-\$ or JP-60184681-\$ or JP-01115162-\$ or JP-04056769-\$ or US-6081446-\$ or EP-291951-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/25 11:00
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	1	((US-5449941-\$ or US-6383576-\$ or US-6166319-\$ or US-5451798-\$ or US-5734181-\$ or US-5260560-\$ or US-5886379-\$ or US-5786250-\$ or US-5877041-\$ or US-5846859-\$ or US-5789276-\$ or US-5754477-\$ or US-5740104-\$ or US-5670790-\$ or US-5714766-\$ or US-5654208-\$ or US-5623442-\$ or US-5580380-\$ or US-5604357-\$ or US-5562769-\$ or US-5557114-\$ or US-5530581-\$ or US-5477485-\$ or US-5455432-\$ or US-5407845-\$ or US-5415126-\$).did. or (US-5298796-\$ or US-5293560-\$ or US-5260593-\$ or US-5235195-\$ or US-5145741-\$ or US-5111430-\$ or US-5049950-\$ or US-4893273-\$ or US-4841349-\$ or US-4769686-\$ or US-4738729-\$ or US-4657699-\$ or US-4462150-\$ or US-4460670-\$ or US-6002143-\$ or US-5852306-\$ or US-4849797-\$ or US-5369040-\$ or US-5039354-\$ or US-5159424-\$ or US-5056897-\$ or US-4826778-\$ or US-5886368-\$ or US-5719410-\$ or US-5371383-\$ or US-6236590-\$ or US-6166948-\$).did. or (US-5793697-\$ or US-5640343-\$ or US-6205052-\$ or US-6178112-\$ or US-6197439-\$ or US-6108177-\$ or US-5408377-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6249020-\$ or US-6018166-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-5661312-\$ or US-5539217-\$ or US-5465249-\$ or US-5323040-\$ or US-4507673-\$ or US-5625217-\$ or US-5061976-\$ or US-6344663-\$ or US-6180958-\$).did. or (US-5989958-\$ or US-5801401-\$ or US-5393999-\$ or US-5629222-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-6351411-\$ or US-5898197-\$ or US-5508543-\$ or US-5808336-\$ or US-5866930-\$ or US-5557122-\$ or US-6034001-\$ or US-5907775-\$ or US-6166401-\$ or US-6163066-\$ or US-6144581-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6031263-\$ or US-6084248-\$ or US-5976926-\$ or US-5698869-\$ or US-4113515-\$ or US-4473836-\$).did. or (US-5858811-\$).did. or (US-20020017647-\$ or US-20020036331-\$ or US-20020041514-\$ or US-20020024050-\$ or US-20010049183-\$ or US-20010032997-\$).did. or (EP-291951-\$ or US-5585986-\$ or EP-681333-\$).did. or (JP-63219172-\$ or JP-01115162-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-04061170-\$ or JP-57126175-\$ or JP-06224431-\$ or JP-63289960-\$).did. or (EP-276002-\$ or JP-07115191-\$ or JP-62122275-\$ or JP-60184681-\$ or JP-01115162-\$ or JP-04056769-\$ or US-6081446-\$ or EP-291951-\$).did.) and miyawaki.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/25 11:00
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-		1	("4460670").PN. ("4462150").PN.	USPAT USPAT USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 17:05 2003/03/25 17:05 2003/08/18 17:38
-		10	(transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:35
-		11	(transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:35
-		1	((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:35
-		8	gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) and 257/\$9.cccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:40
-		0	(gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) and 257/\$9.cccls.) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y)))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:39
-		10	gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:40
-		0	(gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y)))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 18:18
-		2	("5661312").PN.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 09:13
-		0	("jp-57125175\$-\$ did.").PN.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 09:14
-		0	jp-57125175\$-\$ did.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 09:14
-		2	jp-57126175\$-\$ did.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 10:49
-		229	barrier near6 gate and silicon adj carbide	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 09:35
-		5	barrier near6 gate near6 silicon adj carbide	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 10:02

	1	"5506421".PN.	USPAT	2003/08/19 09:37
	1	"5495124".PN.	USPAT	2003/08/19 09:39
	1	"5451797".PN.	USPAT	2003/08/19 09:39
	1	"5396085".PN.	USPAT	2003/08/19 09:43
	1	"5393999".PN.	USPAT	2003/08/19 09:45
	15	gate near6 breakdown near6 (silicon adj carbide "Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x")	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 10:12
	304	"Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x"	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 10:13
	12	("Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x") and gate near6 breakdown	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 10:14
	2	("5369040").PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 10:58
	0	("MOSadjphotodetector.ti,ab.").PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 10:58
	8	MOS adj photodetector.ti,ab.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 11:50
	17	gate near6 polysilicon near6 carbon	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 12:12
	1	"4963953".PN.	USPAT	2003/08/19 12:03
	1	"4780394".PN.	USPAT	2003/08/19 12:04
	1	"4352237".PN.	USPAT	2003/08/19 12:04
	1	"4189826".PN.	USPAT	2003/08/19 12:04
	4	("3497773" "3622382" "3728590" "3896485").PN.	USPAT	2003/08/19 12:07
	43	3896485.URPN.	USPAT	2003/08/19 12:07
	1	MOS adj photodetector.ti,ab,clm. and source and channel and drain	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 12:13
	1	(MOS MOSFET) adj photodetector.ti,ab,clm. and source and channel and drain	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 12:16
	395	photodetector.ti,ab,clm. and source and channel and drain	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 12:17
	100	photodetector.ti,ab,clm.. and source near20 channel near20 drain near20 gate	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 12:17
	0	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 (sic silicon adj carbide)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/08/19 12:19

	1	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 12:23
	7	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 (silicon polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 13:12
	2	("5808336").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 13:13
	51	floating adj gate and photodetector and source and drain and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 13:55
	65	double-poly near12 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 15:12
	0	"4963953".PN.	USPAT	2003/08/19 15:07
	21	((("3792465") or ("4118795") or ("4384349") or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069") or ("5424993") or ("5438544") or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101") or ("5861346") or ("5912837") or ("5926740") or ("6297521") or ("6307775") or ("6309907")).PN.	USPAT	2003/08/19 15:29
	9	((("3792465") or ("4118795") or ("4384349") or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069") or ("5424993") or ("5438544") or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101") or ("5861346") or ("5912837") or ("5926740") or ("6297521") or ("6307775") or ("6309907")).PN.) and (silicon adj carbide or carbon near3 (polysilicon silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:01
	122	silicon adj carbide and monocrystalline and power adj2 (MOS MOSFET device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:02
	59	silicon adj carbide near12 monocrystalline and power adj2 (MOS MOSFET device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:02
	13	silicon adj carbide near12 monocrystalline and power adj2 (MOS MOSFET device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:04
	1430	silicon adj carbide near6 (MOS MOSFET device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:05
	111	silicon adj carbide near6 power near6 (MOS MOSFET device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:05

	55	silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:05
	6	silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm. and monocrystalline near6 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:15
	1811	amorphous adj silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:16
	73	amorphous adj silicon adj carbide and grain adj size	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:16
	2	amorphous adj silicon adj carbide near12 grain adj size	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:32
	23	epitaxial\$2 near12 silicon adj carbide near12 method and (monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:34
	5	epitaxial\$2 near12 silicon adj carbide near12 method near12 (monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:35
	463	method near12 epitaxial\$2 near12 (monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:38
	112	method near12 epitaxial\$2 near12 (monocrystal monocrystalline) and 117/\$6.cc1s.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:59
	112	method near12 epitaxial\$2 near12 crystallinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:59
	0	method near12 epitaxial\$2 near12 crystallinity and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:00
	0	method near12 epitaxial\$2 near12 ensur\$3 near12 crystallinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:00
	49	monocrystalline near4 silicon adj carbide and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:01
	2	monocrystalline near4 silicon adj carbide near6 breakdown and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:02

	2	("5,449,925").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:02
	2	("5449925").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:03
	1	((("5449925").PN.) and epitaxial\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:05
	10	epitaxial\$3 near6 grow\$3 near6 monocrystalline near6 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:08
	14	grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:08
	3	method near6 grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:09
	1	method near6 grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm. and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:09
	16	method near6 (growth growing) near6 (monocrystalline monocrystal) near12 (silicon adj carbide sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:11
	13	method near6 (growth growing) near6 (monocrystalline monocrystal) near12 (silicon adj carbide sic) and epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:20
	2	jp-57126175\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:25
	13	epitaxy near6 (grain crystal) adj size	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:39
	4	(work adj function workfunction) near12 crystallinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:41
	184995	(work adj function workfunction) near12 silicon carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:41
	15	(work adj function workfunction) near12 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:43

-	15	(work adj function workfunction) near12 crystalline near6 amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/19 17:58
-	0	("carbonadjgate").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/19 17:59
-	9657	gate adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/19 17:59
-	0	carbon adj gate and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/19 18:00
-	23	carbon adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/19 18:00
-	19	carbon adj gate and (257/\$9.ccls. 117/\$9.ccls. 438/\$9.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/19 18:03
-	14	"carbon gate" and (257/\$9.ccls. 117/\$9.ccls. 438/\$9.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/19 18:04
-	63	("si.sub.x" adj "c.sub.1-x" or "si.sub.1-x" adj "c.sub.x") and (energy adj gap or band adj energy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/20 10:00
-	132	nanocrystalline and amorphous and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/20 11:47
-	0	nanocrystalline near20 amorphous near20 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/20 11:47
-	4	nanocrystalline same amorphous same silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 12:23

-	157	(US-6121633-\$ or US-6133587-\$ or US-6297521-\$ or US-6306691-\$ or US-6313482-\$ or US-6249020-\$ or US-6365919-\$ or US-6075259-\$ or US-5323040-\$ or US-6130147-\$ or US-5698869-\$ or US-5465249-\$ or US-4113515-\$ or US-4849797-\$ or US-4507673-\$ or US-6031263-\$ or US-5858811-\$ or US-6011279-\$ or US-6049110-\$ or US-5976926-\$ or US-4473836-\$ or US-5734181-\$ or US-6383576-\$ or US-5449941-\$ or US-5393999-\$ or US-5629222-\$).did. or (US-5801401-\$ or US-6166401-\$ or US-6018166-\$ or US-5989958-\$ or US-6180958-\$ or US-6344663-\$ or US-5886368-\$ or US-5039354-\$ or US-4826778-\$ or US-6163066-\$ or US-6084248-\$ or US-6099574-\$ or US-5260560-\$ or US-5159424-\$ or US-5056897-\$ or US-5451798-\$ or US-5369040-\$ or US-6166319-\$ or US-6093937-\$ or US-6144581-\$ or US-5539217-\$ or US-5371383-\$ or US-5719410-\$ or US-5661312-\$ or US-5672889-\$ or US-5798548-\$ or US-5506421-\$).did. or (US-6562131-\$ or US-6547877-\$ or US-6562130-\$ or US-6537371-\$ or US-5030580-\$ or US-4189826-\$ or US-5932902-\$ or US-4598305-\$ or US-5449925-\$ or US-5441901-\$ or US-6236590-\$ or US-4462150-\$ or US-4460670-\$ or US-4657699-\$ or US-5604357-\$ or US-5580380-\$ or US-5623442-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$ or US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5907775-\$).did. or (US-6034001-\$ or US-5886379-\$ or US-5557122-\$ or US-5866930-\$ or US-5808336-\$ or US-5508543-\$ or US-5898197-\$ or US-6351411-\$ or US-6178112-\$ or US-620502-\$ or US-6197439-\$ or US-5640343-\$ or US-5793697-\$ or US-6166948-\$ or US-6307775-\$ or US-4451391-\$ or US-4768072-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-6002143-\$ or US-5852306-\$ or US-6108177-\$ or US-5408377-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$).did. or (US-5293560-\$ or US-5298796-\$ or US-5407845-\$ or US-5415126-\$ or US-5455432-\$ or US-5477485-\$ or US-5530581-\$ or US-5557114-\$ or US-5562769-\$ or US-4841349-\$ or US-4893273-\$ or US-5049950-\$ or US-5111430-\$ or US-4738729-\$ or US-4769686-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020137284-\$ or US-20020036331-\$ or US-20020017647-\$ or US-20020041514-\$ or US-20030001191-\$).did. or (EP-291951-\$ or EP-681333-\$ or US-5585986-\$).did. or (JP-63289960-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-06224431-\$ or JP-57126175-\$ or JP-04061170-\$).did. or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/20 12:07
Search History	9/27/04 1:59:49 PM	PAGE 24		
H:\EASTBACK\09691004	JP-57126175-\$ or JP-04061170-\$).did. or			

-	0	ultra-amorphous near6 nanocrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/20 12:08
-	0	ultra-amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/20 12:08
-	0	ultra adj amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/20 12:08
-	26	carbon adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 12:46
-	4	(carbon adj gate "carbon gate") and float\$3 near4 gate and control adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 13:04
-	2	("4598305").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 13:04
-	2	("4994401").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 13:04
-	439692	SiC "Si.sub."? "C.sub."? silicon adj carbide near6 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 10:29
-	5855	(SiC "Si.sub."? "C.sub."? silicon adj carbide) near6 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 10:29
-	935	(SiC "Si.sub."? "C.sub."? silicon adj carbide) near6 gate and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 10:30
-	74	(SiC "Si.sub."? "C.sub."? silicon adj carbide) near4 gate and barrier and electron adj affinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 13:17
-	74	(SiC "Si.sub."? "C.sub."? silicon adj carbide "SiC.sub.2") near4 gate and barrier and electron adj affinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 13:19
-	0	"SiC.sub.2" near4 gate and barrier and electron adj affinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 13:20
-	1	"SiC.sub.2" near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 13:20
-	30	("SiC.sub.2" carbon near4 (doping doped dopant) near4 (silicon adj carbide SiC)) and gate and (transistor MOSFET MOS NMOS NMOSFET PMOSFET field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 14:44

	2	("6770918").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 15:01
-	0	"SiC.sub.2" near6 gate adj insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 15:02
-	1	"SiC.sub.2" near6 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 15:02
-	0	silicon adj dicarbide and gate and silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 16:24
-	8	("SiC.sub.2" SiC2 silicon adj dicarbide) and gate and silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 17:00
-	1	first adj gate adj insulat\$3 and second adj gate adj insulat\$3 and "SiC.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 16:32
-	1	first adj gate adj insulat\$3 and second adj gate adj insulat\$3 and (SiC2 "SiC.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 16:34
-	38	barrier near4 silicon adj carbide same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 16:43
-	0	(multiple adj gate adj insulat\$3 adj (film layer)) near4 (silicon carbide silicon adj dicarbide SiC2 "Si C.sub.2" "SiC.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 16:46
-	7	("SiC.sub.2" SiC2 silicon adj dicarbide) and gate and silicon adj dioxide and "SiO.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 17:01
-	340	"SiC.sub.2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 17:01
-	27	"SiC.sub.2" and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 17:01
-	1	"SiC.sub.2" near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 17:02
-	5	"SiC.sub.2" same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 17:10

-	2	("5369040").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:13
-	2	903452.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:14
-	6	256643.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:17
-	7	652068.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:17
-	4	652420.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:22
-	3	903486.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:25
-	5	259870.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 17:34
-	5	259870.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:25
-	38	carbon adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:26
-	7	carbon adj gate and floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:28
-	7	"carbon gate" and floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:38
-	0	carbon-gate near4 ISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:38
-	0	carbon-gate near4 pH-ISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:38
-	0	carbon near4 gate near4 pH-ISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:39

	11	carbon near4 gate and pH-ISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 18:40
	11	carbon near8 gate and pH-ISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 18:40
	19	carbon and gate and pH-ISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 18:42
	23145	(carbon C) near8 gate and (pH-ISFET MOSFET transistor CMOSFET MOS CMOS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 18:44
	51	carbon near8 gate and nanotube and field adj effect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/24 18:44
	552	gate near4 (C carbon) near4 (silicon Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:04
	19	gate near4 (C carbon) near4 (silicon Si) near4 (doped doping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:06
	19	gate near4 ("C" carbon) near4 (silicon Si) near4 (doped doping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:10
	257	carbon near5 gate and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:11
	161	carbon near3 gate and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:15
	2	5061976.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:13
	0	Si-doped near4 carbon near3 gate and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:16
	10	doped near4 carbon near3 gate and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:16
	2	(silicon si) near4 doped near4 carbon near3 gate and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:17

	66958	silicon and (anneal annealing) carbon near3 gate and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:18
	1	silicon and (anneal annealing) near4 carbon near4 gate and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:19
	4	silicon near4 (doped doping) near4 carbon near4 gate and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:20
	7	silicon near4 (doped doping) near4 carbon near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:25
	0	"C:Si" near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:25
	64	"C:Si"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:26
	7	"C:Si" and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:35
	4	691004.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:36
	2	903452.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:37
	4	652420.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 13:37
	1	("5369040").PN.	USPAT	2004/09/25 14:17
	542	floating near2 gate and control near2 gate and ((Si silicon) near2 (C carbon) silicon adj carbide "Si.sub."\$2"C.sub."\$2 silicon-doped adj carbon carbon-doped adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 14:23
	151	floating near2 gate and control near2 gate and ((Si silicon) near2 (carbon) silicon adj carbide "Si.sub."\$2"C.sub."\$2 silicon-doped adj carbon carbon-doped adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 16:04
	2	("5801401").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 16:04

-	223	(US-4893273-\$ or US-4841349-\$ or US-4769686-\$ or US-4738729-\$ or US-4657699-\$ or US-4462150-\$ or US-4460670-\$ or US-6125062-\$ or US-6002143-\$ or US-5852306-\$ or US-5449925-\$ or US-6301162-\$ or US-6222778-\$ or US-4426764-\$ or US-6562131-\$ or US-6547877-\$ or US-6562130-\$ or US-6537371-\$ or US-5030580-\$ or US-5907775-\$ or US-5886379-\$ or US-5877041-\$ or US-5846859-\$ or US-5789276-\$ or US-5786250-\$ or US-5754477-\$).did. or (US-5740104-\$ or US-5714766-\$ or US-5670790-\$ or US-5654208-\$ or US-5623442-\$ or US-5604357-\$ or US-5580380-\$ or US-5562769-\$ or US-5557114-\$ or US-5530581-\$ or US-5477485-\$ or US-5455432-\$ or US-5415126-\$ or US-5407845-\$ or US-5298796-\$ or US-5293560-\$ or US-5260593-\$ or US-5235195-\$ or US-5145741-\$ or US-5111430-\$ or US-5049950-\$ or US-5672889-\$ or US-5661312-\$ or US-5539217-\$ or US-5506421-\$ or US-5465249-\$ or US-5323040-\$).did. or (US-4507673-\$ or US-6018166-\$ or US-5625217-\$ or US-5061976-\$ or US-4943838-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-6307775-\$ or US-6351411-\$ or US-5898197-\$ or US-5508543-\$ or US-5808336-\$ or US-5866930-\$ or US-5557122-\$ or US-6034001-\$ or US-5393999-\$ or US-6383576-\$ or US-6166319-\$ or US-5734181-\$ or US-5451798-\$ or US-5369040-\$ or US-5260560-\$ or US-5159424-\$ or US-5056897-\$ or US-5039354-\$ or US-4826778-\$).did. or (US-5886368-\$ or US-5719410-\$ or US-5371383-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6297521-\$ or US-6249020-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-6099574-\$ or US-6093937-\$ or US-6084248-\$ or US-4473836-\$ or US-4113515-\$ or US-4849797-\$ or US-6344663-\$ or US-6180958-\$ or US-6133120-\$ or US-5989958-\$ or US-5801401-\$ or US-5629222-\$ or US-5449941-\$).did. or (US-6144581-\$ or US-6130147-\$ or US-6031263-\$ or US-5976926-\$ or US-5858811-\$ or US-5698869-\$ or US-4994401-\$ or US-6166401-\$ or US-6163066-\$ or US-4598305-\$ or US-5932902-\$ or US-4373167-\$ or US-4189826-\$ or US-6492694-\$ or US-6723581-\$ or US-6141260-\$ or US-6304493-\$ or US-6297994-\$ or US-6407426-\$ or US-6452831-\$ or US-6452839-\$ or US-6465375-\$ or US-6514820-\$ or US-6563260-\$ or US-6731531-\$ or US-6734510-\$ or US-6746893-\$).did. or (US-6754108-\$ or US-6762068-\$ or US-6778441-\$ or US-6781876-\$ or US-6794255-\$ or US-6573169-\$ or US-6586797-\$ or US-5441901-\$ or US-6300193-\$ or US-6407424-\$ or US-6630375-\$ or US-6746921-\$ or US-6197439-\$ or US-5640343-\$ or US-5793697-\$ or US-6166948-\$ or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/25 18:18
Search History	9/27/04 5:59:49 PM	Page 40		
H:\EASTBACK\09691004	US-5793697-\$ or US-6166948-\$ or			

		47	control adj (gates gate) and floating adj (gates gate) near4 (silicon adj carbide "SiC")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 17:30
		2	6309907.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 17:32
		2	("5886368").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 17:42
		3	902843.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 17:49
		23	((("4598305") or ("4980303") or ("4994401") or ("5189504") or ("5336361") or ("5367306") or ("5409501") or ("5990531") or ("6100193") or ("6166768") or ("6365919")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 17:51
		25	((("4598305") or ("4980303") or ("4994401") or ("5189504") or ("5336361") or ("5367306") or ("5409501") or ("5990531") or ("6100193") or ("6166768") or ("6365919") or ("5471515")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 17:51
		1	135413.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/25 18:19
		7	134713.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/25 18:22
		33	"6031263"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/25 18:23
		2	("6031263").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/25 18:24
		2	("6307775").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 18:24
		2	("6249020").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 18:29
		16	((("5798548") or ("5808336") or ("5828101") or ("5861346") or ("5886376") or ("5976926") or ("5989958") or ("5990531") or ("6084248") or ("6093937") or ("6099574") or ("6100193") or ("6130147") or ("6166768") or ("6271566") or ("6365919")).PN.	USPAT	2004/09/25 18:34
		2	902133.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 18:38

-	6	(("5336361") or ("5990531") or ("6166768")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:05
-	4	(("5910665") or ("6049091")).PN.		2004/09/25 18:55
-	3	231687.ap.		2004/09/25 18:56

-	233	(US-4598305-\$ or US-5441901-\$ or US-6108177-\$ or US-5408377-\$ or US-6205052-\$ or US-6563260-\$ or US-6514820-\$ or US-6734510-\$ or US-6731531-\$ or US-6178112-\$ or US-6236590-\$ or US-6166948-\$ or US-5793697-\$ or US-5640343-\$ or US-6197439-\$ or US-6465375-\$ or US-6452839-\$ or US-6452831-\$ or US-6723581-\$ or US-6492694-\$ or US-4189826-\$ or US-4373167-\$ or US-5932902-\$ or US-6407426-\$ or US-6297994-\$ or US-6304493-\$).did. or (US-6141260-\$ or US-5910665-\$ or US-5861346-\$ or US-5336361-\$ or US-6049091-\$ or US-5828101-\$ or US-5990531-\$ or US-6100193-\$ or US-6300193-\$ or US-5886376-\$ or US-5959896-\$ or US-6407424-\$ or US-6246606-\$ or US-6746921-\$ or US-6630375-\$ or US-6140181-\$ or US-6271566-\$ or US-6166768-\$ or US-5061976-\$ or US-4943838-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5654208-\$).did. or (US-5670790-\$ or US-5714766-\$ or US-6778441-\$ or US-6781876-\$ or US-6762068-\$ or US-6794255-\$ or US-5719410-\$ or US-5371383-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6297521-\$ or US-6249020-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-5672889-\$ or US-5661312-\$ or US-5539217-\$ or US-5506421-\$ or US-5465249-\$ or US-5323040-\$ or US-4507673-\$ or US-6018166-\$).did. or (US-5625217-\$ or US-4849797-\$ or US-6344663-\$ or US-6180958-\$ or US-6133120-\$ or US-5989958-\$ or US-5801401-\$ or US-5629222-\$ or US-5449941-\$ or US-5393999-\$ or US-6383576-\$ or US-6166319-\$ or US-5734181-\$ or US-5451798-\$ or US-5369040-\$ or US-5260560-\$ or US-5159424-\$ or US-5056897-\$ or US-5039354-\$ or US-4826778-\$ or US-5886368-\$ or US-6099574-\$ or US-6144581-\$ or US-6166401-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$).did. or (US-6093937-\$ or US-5858811-\$ or US-5698869-\$ or US-4113515-\$ or US-4473836-\$ or US-6163066-\$ or US-6130147-\$ or US-6573169-\$ or US-6586797-\$ or US-5449925-\$ or US-4738729-\$ or US-4769686-\$ or US-4841349-\$ or US-4893273-\$ or US-5049950-\$ or US-5111430-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$ or US-5293560-\$ or US-5298796-\$ or US-5407845-\$ or US-5415126-\$ or US-5455432-\$ or US-5477485-\$ or US-5530581-\$ or US-5557114-\$).did. or (US-6754108-\$ or US-5562769-\$ or US-6746893-\$ or US-4994401-\$ or US-5030580-\$ or US-6537371-\$ or US-6562130-\$ or US-6547877-\$ or US-6562131-\$ or US-4426764-\$ or US-6222778-\$ or US-6301162-\$ or US-4657699-\$ or US-4162150-\$ or US-5846859-\$ or US-5877041-\$ or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/25 19:01
Search History	9/27/04 7:59:49 PM	Page 23		
H:\EASTBACK\09691004	US-5846859-\$ or US-5877041-\$ or			

-	0	carbon-doped near4 silicon near4 floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:01
-	0	carbon near4 (doped dopant) near4 silicon near4 floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:03
-	0	c-doped near4 silicon near4 floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:03
-	2	("6746893").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:19
-	2	("6762068").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:22
-	2	("5949483").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:33
-	0	micron.as. and floating.clm. and (reset control).clm. and "Si.sub."\$2"C.sub."\$2.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:35
-	145	micron.as. and floating.clm. and (reset control).clm. and (silicon carbide "Si.sub."\$2"C.sub."\$2).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:36
-	4	902132.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:40
-	5	259870.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:45
-	7	138294.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 19:58
-	2	("5886368").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 20:22
-	0	("903453.ap.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 20:23
-	3	903453.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 20:23

-	233	(US-6762068-\$ or US-6778441-\$ or US-6746893-\$ or US-6746921-\$ or US-6731531-\$ or US-6734510-\$ or US-6723581-\$ or US-6630375-\$ or US-6586797-\$ or US-6573169-\$ or US-6563260-\$ or US-6547877-\$ or US-6562130-\$ or US-6537371-\$ or US-6562131-\$ or US-6492694-\$ or US-6514820-\$ or US-6452839-\$ or US-6465375-\$ or US-6383576-\$ or US-6407424-\$ or US-6407426-\$ or US-6452831-\$ or US-6351411-\$ or US-6365919-\$ or US-6344663-\$). did. or (US-6309907-\$ or US-6313482-\$ or US-6307775-\$ or US-6306691-\$ or US-6297994-\$ or US-6300193-\$ or US-6301162-\$ or US-6304493-\$ or US-6249020-\$ or US-6297521-\$ or US-6205052-\$ or US-6222778-\$ or US-6236590-\$ or US-6246606-\$ or US-6180958-\$ or US-6197439-\$ or US-6794255-\$ or US-6781876-\$ or US-4738729-\$ or US-4768072-\$ or US-4507673-\$ or US-4598305-\$ or US-4657699-\$ or US-4462150-\$ or US-5056897-\$ or US-4994401-\$ or US-5039354-\$). did. or (US-4473836-\$ or US-4460670-\$ or US-4113515-\$ or US-4189826-\$ or US-4373167-\$ or US-4426764-\$ or US-4451391-\$ or US-6100193-\$ or US-5990531-\$ or US-6166768-\$ or US-5336361-\$ or US-6271566-\$ or US-6049091-\$ or US-5861346-\$ or US-5828101-\$ or US-5910665-\$ or US-4849797-\$ or US-4893273-\$ or US-4769686-\$ or US-4826778-\$ or US-5030580-\$ or US-4943838-\$ or US-4841349-\$ or US-5049950-\$ or US-5623442-\$ or US-5530581-\$ or US-5539217-\$). did. or (US-5557114-\$ or US-5557122-\$ or US-5506421-\$ or US-5508543-\$ or US-5455432-\$ or US-5465249-\$ or US-5477485-\$ or US-5449941-\$ or US-5451798-\$ or US-5407845-\$ or US-5408377-\$ or US-5415126-\$ or US-5441901-\$ or US-5449925-\$ or US-6099574-\$ or US-6108177-\$ or US-5369040-\$ or US-5393999-\$ or US-5371383-\$ or US-5323040-\$ or US-5298796-\$ or US-5293560-\$ or US-5260560-\$ or US-5260593-\$ or US-5159424-\$ or US-5235195-\$ or US-5145741-\$). did. or (US-5061976-\$ or US-5111430-\$ or US-6133120-\$ or US-5976926-\$ or US-5907775-\$ or US-5932902-\$ or US-5852306-\$ or US-5858811-\$ or US-5866930-\$ or US-5798548-\$ or US-5801401-\$ or US-6049110-\$ or US-6075259-\$ or US-5989958-\$ or US-6002143-\$ or US-6011279-\$ or US-5886379-\$ or US-5898197-\$ or US-5877041-\$ or US-6034001-\$ or US-6031263-\$ or US-6018166-\$ or US-6093937-\$ or US-6084248-\$ or US-6130147-\$ or US-5959896-\$ or US-5886368-\$). did. or (US-5886376-\$ or US-5670790-\$ or US-5672889-\$ or US-5698869-\$ or US-5714766-\$ or US-5640343-\$ or US-5654208-\$ or US-5661312-\$ or US-5625217-\$ or US-5629222-\$ or US-5562769-\$ or US-5580380-\$ or US-5604357-\$ or US-5808336-\$ or US-5846859-\$ or US-5786250-\$ or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/27 07:36
Search History	9/27/04 7:59:19 PM	Page 45		
H:\EASTBACK\09691004	US-5846859-\$ or US-5786250-\$ or			

-	19	carbon near4 gate and floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 08:18
-	2	("6309907").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 08:26
-	0	floating adj gate and control adj gate and silicon adj dioxide near3 (interlayer adj dielectric ild) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 08:31
-	0	floating adj gate and silicon adj dioxide near3 (interlayer adj dielectric ild) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 08:31
-	34	floating adj gate and silicon adj dioxide and (interlayer adj dielectric ild) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 09:18
-	4	691004.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 10:54
-	170	floating adj gate and control adj gate and (silicon adj carbide SiC)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 10:55
-	47	floating adj gate near4 (silicon adj carbide SiC) and control adj gate and (memory eprom)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 11:05
-	52	floating adj gate near4 (silicon adj carbide SiC)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 11:05
-	5	floating adj gate near4 (silicon adj carbide SiC) not (floating adj gate near4 (silicon adj carbide SiC) and control adj gate and (memory eprom))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 11:10
-	2	903452.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 11:11
-	5	746893.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 11:11
-	2	6746893.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 13:41
-	0	eprom near5 (p-type n-type) near5 (preferabl\$1 advantage\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 13:42

